

2"GaAs Wafer Specification—P type

Conduct Type	Semi-conducting
Crystal Growth Method	VGF
Type	P
Dopant	Zn
Diameter	50.8±0.4mm
Orientation	(100) 0°±0.5°
Primary Flat	EJ [0`1`1] ±0.5°
Primary Flat Length	16±1
Secondary Flat	EJ [0`1`1] ±0.5°
Secondary Flat Length	7±1
Carrier Concentration	(1-5)E19/cm ³
Resistivity	N/A
Mobility	N/A
EPD	<5000 /cm ²
Thickness	350±25m
Polishing	P/E
Package	Single wafer box Epi-Ready